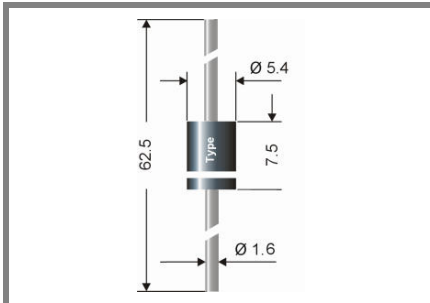


# SBH 1220TL ... SBH 1245TL



## Axial lead diode

Type	Repetitive peak reverse voltage $V_{RRM}$ V	Surge peak reverse voltage $V_{RSM}$ V	Max. reverse recovery time $I_F = -A$ $I_R = -A$ $I_{RR} = -A$ $t_{rr}$ ns	Max. forward voltage $V_F^{(2)}$
SBH 1220TL	20	20	-	0,51
SBH 1230TL	30	30	-	0,51
SBH 1240TL	40	40	-	0,51
SBH 1245TL	45	45	-	0,51

## High temperature Schottky barrier diodes

### SBH 1220TL ... SBH 1245TL

**Forward Current: 12 A**

**Reverse Voltage: 20 to 45 V**

Preliminary Data

### Features

- Max. solder temperature: 260°C
- Plastic material has UL classification 94V-0

### Mechanical Data

- Plastic case: 5,4 x 7,5 [mm]
- Weight approx.: 1,6 g
- Terminals: plated terminals solderable per MIL-STD-750
- Mounting position: any
- Standard packaging: 1250 pieces per ammo or per reel

- 1) Valid, if leads are kept at ambient temperature at a distance 0mm from case
- 2)  $I_F = 5 A$ ,  $V_F < 600 mV$  @  $I_F = 12 A$ ,  $T_j = 25 ^\circ C$
- 3)  $T_A = 25 ^\circ C$
- 4) Thermal resistance from junction to lead/terminal at a distance 0 mm from case
- 5) Max. junction temperature  $T_j \leq 200 ^\circ C$  in reverse mode  $V_R = 80\% V_{RRM}$  and in bypass mode / DC forward mode

Absolute Maximum Ratings		$T_A = 25 ^\circ C$ , unless otherwise specified	
Symbol	Conditions	Values	Units
$I_{FAV}$	Max. averaged fwd. current, R-load, $T_A = 75 ^\circ C$ <sup>1)</sup>	12	A
$I_{FRM}$	Repetitive peak forward current $f > 15 Hz$ <sup>1)</sup>	55	A
$I_{FSM}$	Peak forward surge current 50 Hz half sinus-wave <sup>3)</sup>	300	A
$i^2t$	Rating for fusing, $t < 10 ms$ <sup>3)</sup>	450	A <sup>2</sup> s
$R_{thA}$	Max. thermal resistance junction to ambient <sup>1)</sup>		K/W
$R_{thL}$	Max. thermal resistance junction to terminals <sup>4)</sup>	2	K/W
$T_j$	Operating junction temperature	- 50 ... + 200	°C
$T_s$	Storage temperature	- 50 ... + 200	°C

Characteristics		$T_A = 25 ^\circ C$ , unless otherwise specified	
Symbol	Conditions	Values	Units
$I_R$	Maximum leakage current, $T_j = 25 ^\circ C$ ; $V_R = V_{RRM}$	<50	µA
	$T_j = 100 ^\circ C$ ; $V_R = V_{RRM}$	<2,5	mA
$C_j$	Typical junction capacitance (at MHz and applied reverse voltage of V)	-	pF
$Q_{rr}$	Reverse recovery charge ( $U_R = V$ ; $I_F = A$ ; $dI_F/dt = A/ms$ )	-	µC
$E_{RSM}$	Non repetitive peak reverse avalanche energy ( $I_R = mA$ ; $T_j = ^\circ C$ ; inductive load switched off)	-	mJ

